

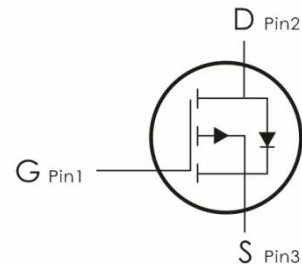
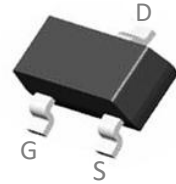
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-100V, I_D=-2A, R_{DS(ON)}<330m\Omega @V_{GS}=-10V$ (Typ: $305m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
VH360PG	H360P	SOT-23-3	3000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_A=25^\circ\text{C}^1$	-2	A
	Continuous Drain Current- $T_A=100^\circ\text{C}^1$	-1.4	
I_{DM}	Pulsed Drain Current ²	-8	
P_D	Power Dissipation	1.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	73.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-100	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-100V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1	-1.7	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =-10V, I _D =-1A	---	305	330	m Ω
		V _{GS} =-4.5V, I _D =-1A	---	330	360	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	1089	---	pF
C _{oss}	Output Capacitance		---	32	---	
C _{rss}	Reverse Transfer Capacitance		---	25	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-50V, I _D =-1A, R _{ENG} =10 Ω ,V _{GS} =-10V	---	10	---	ns
t _r	Rise Time		---	14	---	ns
t _{d(off)}	Turn-Off Delay Time		---	27	---	ns
t _f	Fall Time		---	23	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-50V, I _D =-1A	---	20	---	nC
Q _{gs}	Gate-Source Charge		---	2	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	2.6	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =-1A	---	---	-1.2	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	-1.6	A
I _{SM}	Pulsed Drain Current		---	---	-6.6	A
T _{rr}	Reverse Recovery Time	I _F =1A, T _J =25 °C	---	30	---	ns
Q _{rr}	Reverse Recovery Charge	dl/dt=100A/us	---	35	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Test Circuit

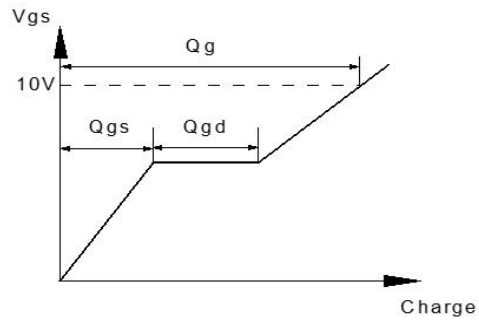
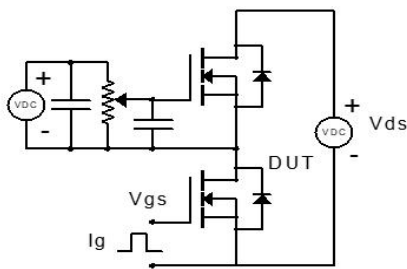


Figure 1: Gate Charge Test Circuit & Waveform

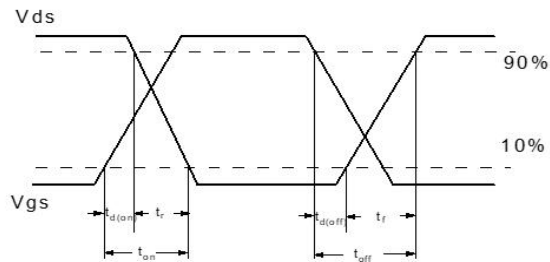
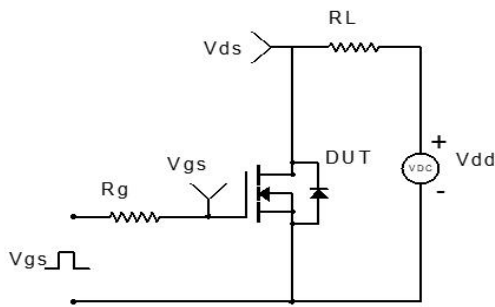


Figure 2: Resistive Switching Test Circuit & Waveform

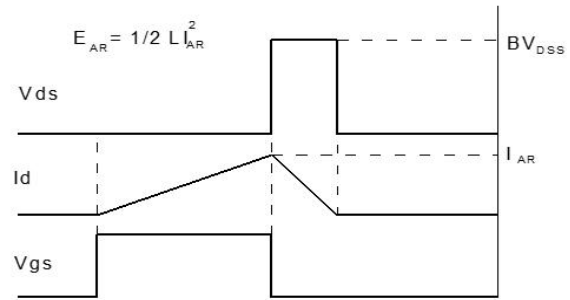
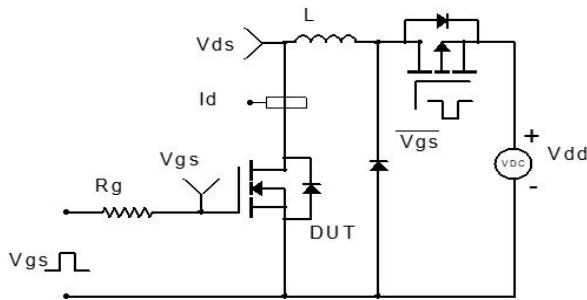


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

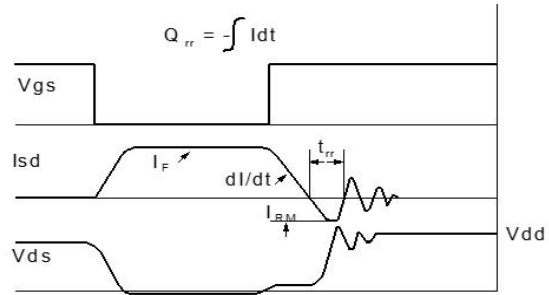
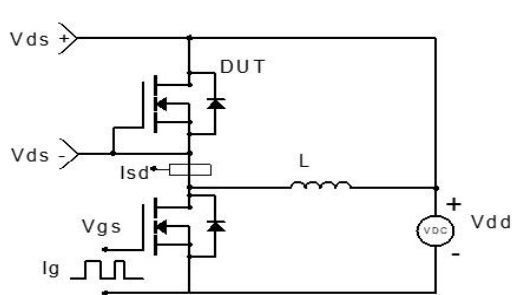
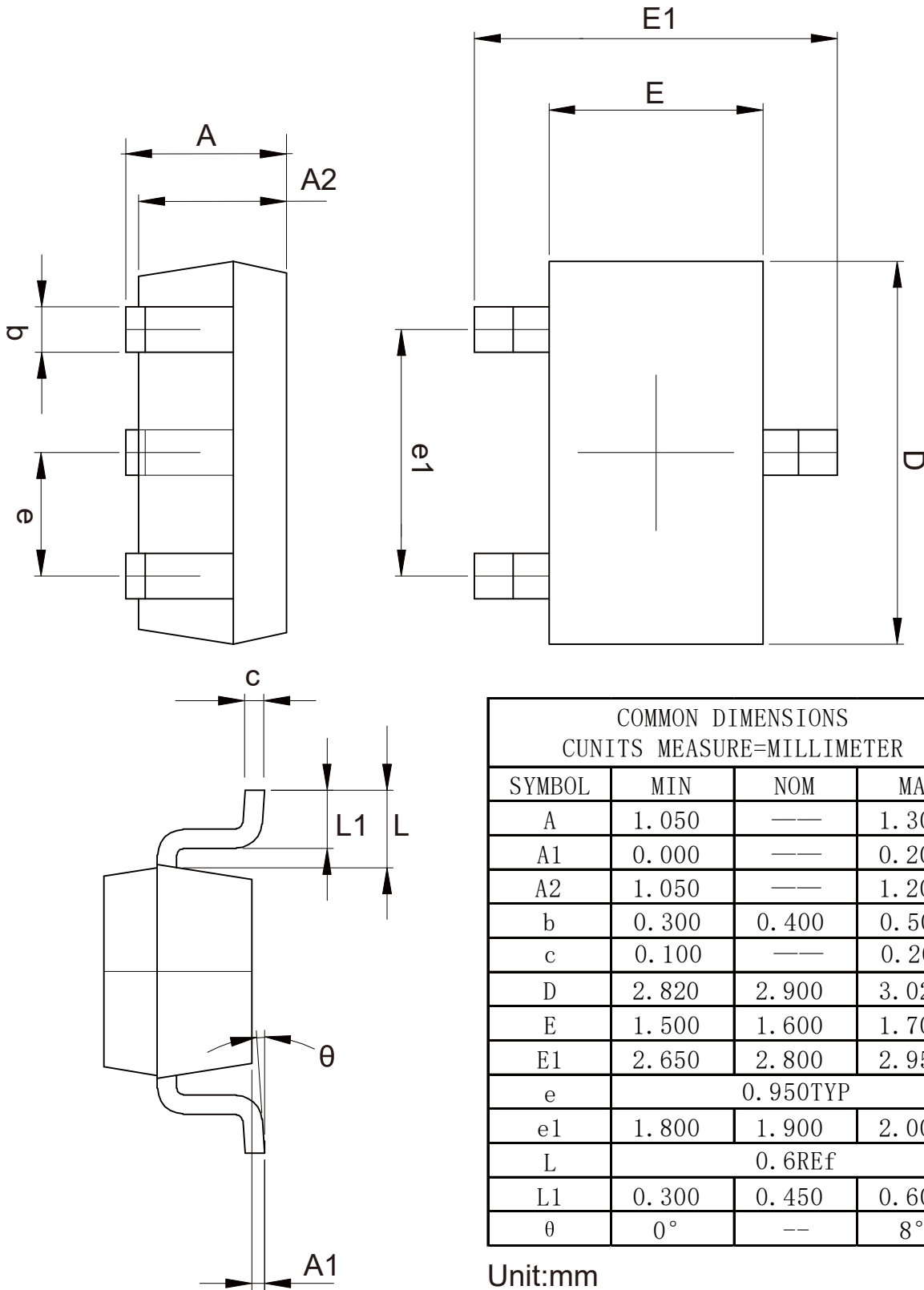


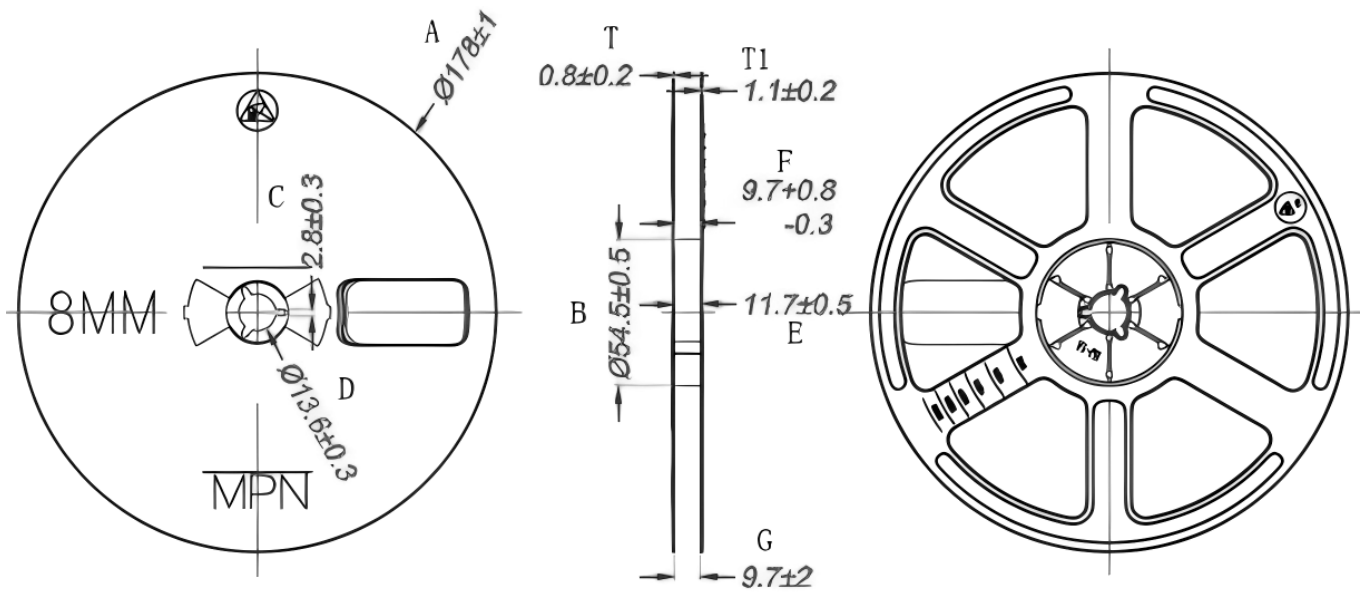
Figure 4: Diode Recovery Test Circuit & Waveform

SOT-23-3 Package Outline Data

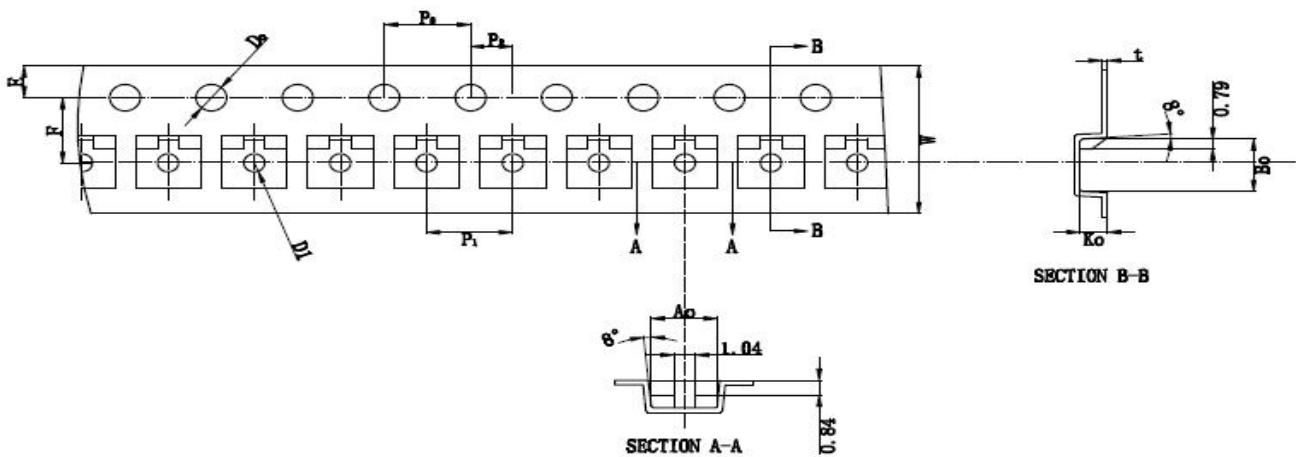


Tape & Reel Information

Dimensions in mm

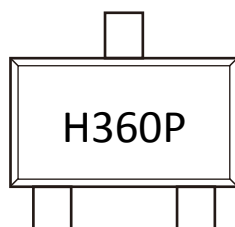


PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT23-3	8.00	4.00	1.75	3.50	1.50	1.00	4.00	40.00	2.00	3.13	3.22	1.30	0.20
Tolerance	± 0.2	± 0.1	± 0.1	± 0.1	± 0.1	± 0.1	± 0.1	± 0.2	± 0.1	± 0.1	± 0.1	± 0.1	± 0.03



Pulling direction 

Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
1.1	2025-09-26	Release of final version

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